IN THE CLAIMS:

- (Currently Amended) A semiconductor light emitting device comprising: a substrate;
- a plurality of semiconductor blue-light emitting elements each having an epitaxial structure on the substrate;
- a plurality of semiconductor red-light emitting elements that have been mounted on an electrically conductive pattern provided on the substrate; and
- a phosphor that covers the semiconductor blue-light emitting elements and the semiconductor red-light emitting elements, wherein
- each semiconductor red-light emitting element has been flip-chip mounted via at

 10 least one bump.
 - a vertical height of each semiconductor red-light emitting element from a main surface of the substrate is greater than a vertical height of each semiconductor blue-light emitting element from the main surface of the substrate, and
- the semiconductor red-light emitting elements and the semiconductor blue-light

 emitting elements are arranged in a matrix, in such a manner that each semiconductor red-light

 emitting element is adjacent to semiconductor blue-light emitting elements in both row and

 column directions, except for some of the semiconductor blue-light emitting elements which are

 at corners of the substrate.
- a plurality of pairs of pads that are on the substrate and together with the

 20 semiconductor blue-light emitting elements, arranged in a matrix, in such a manner that each pair

of pads is adjacent to a different one of the semiconductor blue light emitting elements in a row and column direction; and

a plurality of semiconductor red light emitting elements that are each mounted on a different one of the pairs of pads, wherein a height of each semiconductor red light emitting element from the substrate is greater than a height of each semiconductor blue light emitting element from the substrate.

2.-3. (Cancelled)

- 4. (Currently Amended) The semiconductor light emitting device of Claim 1, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:
- a phosphor that covers the blue LEDs and the red LEDs and converts blue light
 emitted by the blue LEDs into green-yellow light the phosphor converts blue light emitted by the
 blue LEDs into green-yellow light.
 - (Previously Presented) The semiconductor light emitting device of Claim 4, wherein the red light, which is emitted by the red LEDs, has a peak emission wavelength within a range of 615 nm and 635 nm.

the blue light has a peak emission wavelength within a range of 450 nm and 470 $\,$

5 nm, and

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the green-yellow light has a peak emission wavelength within a range of 540 nm and 560 nm.

- (Original) The semiconductor light emitting device of Claim 5, wherein
 the red light has a peak emission wavelength within a range of 620 nm and 630
 nm,
- - the green-yellow light has a peak emission wavelength within a range of 545 nm and 555 nm.
 - (Original) The semiconductor light emitting device of Claim 4, wherein the phosphor is a silicate phosphor (Ba, Sr)₂SiO₄:Eu²⁺.
 - (Original) The semiconductor light emitting device of Claim 4, wherein the substrate is made of one of SiC and AlN materials.
 - (Previously Presented) The semiconductor light emitting device of Claim 4, further comprising:
 - a wiring pattern that electrically connects the blue LEDs and the red LEDs together.
 - (Previously Presented) The semiconductor light emitting device of Claim 9, wherein
 - the wiring pattern connects the blue LEDs and the red LEDs together in series.
 - 11.-15. (Cancelled)

- (Currently Amended) A light emitting module comprising:
 - a printed-wiring board; and
 - a semiconductor light emitting device including:
 - a substrate:

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- a plurality of semiconductor blue-light emitting elements each having an epitaxial structure on the substrate:
- a plurality of pairs of pads that are on the substrate and together with the semiconductor blue light emitting elements, arranged in a matrix, in such a manner that each pair of pads is adjacent to a different one of the semiconductor blue light emitting elements in a row and column direction; and
- a plurality of semiconductor red-light emitting elements that are each mounted on a different one of the pairs of pads, wherein a height of each semiconductor red light element from the substrate is greater than a height of each semiconductor blue light emitting element from the substrate, mounted on the printed wiring board have been mounted on an electrically conductive pattern provided on the substrate; and
- a phosphor that covers the semiconductor blue-light emitting elements and the semiconductor red-light emitting elements, wherein
- each semiconductor red-light emitting element has been flip-chip mounted via at least one bump.
- a vertical height of each semiconductor red-light emitting element from a main surface of the substrate is greater than a vertical height of each semiconductor blue-light emitting element from the main surface of the substrate, and

the semiconductor red-light emitting elements and the semiconductor blue-light emitting elements are arranged in a matrix, in such a manner that each semiconductor red-light emitting element is adjacent to semiconductor blue-light emitting elements in both row and column directions, except for some of the semiconductor blue-light emitting elements which are at corners of the substrate.

- 17. (Previously Presented) The light emitting module of Claim 16, further comprising:
- a lighting apparatus including a closed structure in which the light emitting module is disposed.
- 18. (Currently Amended) The light emitting module of Claim 16, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:
- a phosphor that covers the blue LEDs and the red LEDs and converts blue light emitted by the blue LEDs into green vellow light and the phosphor converts blue light emitted 5 by the blue LEDs into green-yellow light.
 - (Previously Presented) The light emitting module of Claim 18, wherein red light, 19. which is emitted by the red LEDs, has a peak emission wavelength within a range of 615 nm and 635 nm.
- the blue light has a peak emission wavelength within a range of 450 nm and 470 5
 - the green-yellow light has a peak emission wavelength within a range of 540 nm and 560 nm.

nm, and

 (Previously Presented) The light emitting module of Claim 18, wherein the red light has a peak emission wavelength within a range of 620 nm and 630 nm,

the blue light has a peak emission wavelength within a range of 455 nm and 465 nm, and

- the green-yellow light has a peak emission wavelength within a range of 545 nm and 555 nm.
 - 21. (Previously Presented) The light emitting module of Claim 18, wherein the phosphor is a silicate phosphor (Ba, Sr)₂SiO₄:Eu²⁺.
 - (Previously Presented) The light emitting module of Claim 16, wherein the substrate is made of one of SiC and AlN materials.
 - 23. (Previously Presented) The light emitting module of Claim 16, further comprising:
 - a wiring pattern that electrically connects the blue LEDs and the red LEDs together.
 - (Previously Presented) The light emitting module of Claim 23, wherein the wiring pattern connects the blue LEDs and the red LEDs together in series.
 - (Currently Amended) A method for manufacturing a semiconductor light emitting device comprising:

providing a substrate;

growing a plurality of semiconductor blue-light emitting elements on the substrate

5 with an epitaxial structure;

forming a plurality of pairs of pads on the substrate in such a manner that each
pair of pads is adjacent to a different one of the semiconductor blue light emitting elements in a
row and column direction; and

mounting providing a plurality of semiconductor red-light emitting elements on an electrically conductive pattern provided on the substrate; and a different one of the pairs of pads, wherein a height of each semiconductor red light emitting element from the substrate is greater than a height of each semiconductor blue light emitting element from the substrate.

providing a phosphor that covers the semiconductor blue-light emitting elements and the semiconductor red-light emitting elements, wherein

the semiconductor red-light emitting elements are provided by flip-chip mounting each semiconductor red-light emitting element via at least one bump.

a vertical height of each semiconductor red-light emitting element from a main surface of the substrate is greater than a vertical height of each semiconductor blue-light emitting element from the main surface of the substrate, and

the semiconductor red-light emitting elements and the semiconductor blue-light emitting elements are arranged in a matrix, in such a manner that each semiconductor red-light emitting element is adjacent to semiconductor blue-light emitting elements in both row and column directions, except for some of the semiconductor blue-light emitting elements which are at corners of the substrate.

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26. (Currently Amended) The method of Claim 25, wherein each semiconductor blue-light emitting element comprises a blue LED, and each semiconductor red-light emitting element comprises a red LED, and further comprising:

eovering the blue LEDs and the red LEDs with a the phosphor [[that]] converts

blue light emitted by the blue LEDs into green-yellow light.

27. (Previously Presented) The method of Claim 25, further comprising: forming a wiring pattern that electrically connects the blue LEDs and the red LEDs together.